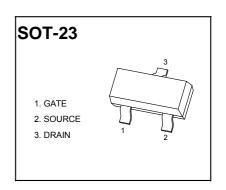


# **SOT-23 Plastic-Encapsulate MOSFETS**

#### 20V P-Channel MOSFET

| V <sub>(BR)DSS</sub> | R <sub>DS(on)</sub> Typ | I <sub>D</sub> Max |
|----------------------|-------------------------|--------------------|
| -20V                 | 37mΩ@ -4.5V             | -4.8A              |
| -20 V                | 43mΩ@ -3.3V             |                    |



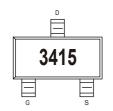
#### **FEATURE**

Excellent R<sub>DS(ON)</sub>, low gate charge,low gate voltages

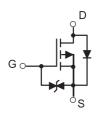
### **APPLICATION**

Load switch and in PWM applicatopns

### **MARKING**



## **Equivalent circuit**



#### **PACKAGE SPECIFICATIONS**

| Package | Reel Size | Reel DIA.<br>(mm) | Q'TY/Reel<br>(pcs) | Box Size (mm) | QTY/Box<br>(pcs) | Carton Size (mm) | Q'TY/Carton<br>(pcs) |
|---------|-----------|-------------------|--------------------|---------------|------------------|------------------|----------------------|
| SOT-23  | 7'        | 178               | 3000               | 203×203×195   | 45000            | 438×438×220      | 180000               |

## Maximum Ratings and Thermal Characteristics (TA = 25°C unless otherwise noted)

| Parameter   | Symbol                 | Limit                             | Unit       |      |  |
|---|------------------------|-----------------------------------|------------|------|--|
| Drain-Source Voltage                                    | $V_{(BR)DSS}$          | -20                               | V          |      |  |
| Gate-Source Voltage                                     | $V_{GS}$               | ±8                                | V          |      |  |
|   | T <sub>A</sub> = 25 °C |                                   | -4.8       | Α    |  |
| Continuous Drain Current                                | T <sub>A</sub> = 70°C  | -j I <sub>D</sub> [               | -3.6       |      |  |
| Pulsed Drain Current 1)                                 | •                      | I <sub>DM</sub>                   | -30        | Α    |  |
| Maximum Power Dissipation <sup>2)</sup>                 | T <sub>A</sub> = 25 °C | Po                                | 1.5        | 10/  |  |
|   | T <sub>A</sub> = 70°C  | 10                                | 1.0        | W    |  |
| Operating Junction and Storage Temperature Range        |                        | T <sub>J</sub> , T <sub>stg</sub> | -50 to 150 | °C   |  |
| Junction-to-Ambient Thermal Resistance (PCB mounted) 2) |                        | R <sub>thJA</sub>                 | 80         | °C/W |  |

2) Surface Mounted on FR4 Board,  $t \le 5$  sec.

The above data are for reference only.

Notes
1) Pulse width limited by maximum junction temperature.



## MOSFET ELECTRICAL CHARACTERISTICS

# T<sub>a</sub>=25 °C unless otherwise specified

| Parameter                               | Symbol           | Test Condition   | Min | Тур   | Max  | Units |  |
|---|------------------|--|-----|-------|------|-------|--|
| Static Parameters                       |                  |  |     |       |      |       |  |
| Drain-source breakdown voltage          | V(BR) DSS        | V <sub>G</sub> S = 0V, I <sub>D</sub> =-250µA                    | -20 |       |      | V     |  |
| Gate threshold voltage                  | VGS(th)          | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA        |     | -0.7  | -1.2 | V     |  |
| Zero gate voltage drain current         | I <sub>DSS</sub> | V <sub>DS</sub> =20V, V <sub>GS</sub> =0V (TA=25℃)               |     |       | -1   |       |  |
| Zero gate voltage drain current         | .033             | V <sub>DS</sub> =16V, V <sub>GS</sub> =0V (TA=125℃)              |     |       | -100 | μΑ    |  |
| Gate-body leakage current               | I <sub>GSS</sub> | V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V                        |     |       | ±10  |       |  |
|   | RDS(on)          | V <sub>G</sub> S =-4.5V, I <sub>D</sub> =-4A                     |     | 37    | 45   | mΩ    |  |
| Drain-source on-state resistance(note1) |                  | Vgs =-3.3V, ID =-3A  |     | 43    | 55   |       |  |
|   |                  | Vgs =-2.5V, ID =-2A  |     | 52    | 65   |       |  |
| Forward transconductance(note2)         | <b>g</b> FS      | V <sub>DS</sub> =-5V, I <sub>D</sub> =-4A                        | 8   |       |      | S     |  |
| Dynamic Parameters (note3)              |                  |  |     |       |      |       |  |
| Input capacitance                       | C <sub>iss</sub> |  |     | 675   |      | pF    |  |
| Output capacitance                      | Coss             | V <sub>DS</sub> =-10V,V <sub>GS</sub> =0V,f =1MHz                |     | 120   |      |       |  |
| Reverse transfer capacitance            | C <sub>rss</sub> |  |     | 85    |      |       |  |
| Gate resistance                         | Rg               | V <sub>DS</sub> =0V,V <sub>GS</sub> =0V,f =1MHz                  |     | 6.5   |      | Ω     |  |
| Switching Parameters                    |                  |  |     |       |      |       |  |
| Total gate charge                       | Qg               |  |     | 14.2  |      |       |  |
| Gate-Source charge                      | Qgs              | V <sub>DS</sub> =-10V,V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-4A |     | 3.2   |      | nC    |  |
| Gate-drain charge                       | $Q_{gd}$         |  |     | 5.8   |      |       |  |
| Turn-on delay time (note3)              | td(on)           |  |     | 15    |      |       |  |
| Turn-on rise time(note3)                | tr               | V <sub>DS</sub> =-10V, V <sub>GS</sub> =-4.5V                    |     | 11    |      | ns    |  |
| Turn-off delay time(note3)              | td(off)          | RGEN =3 $\Omega$ , R <sub>L</sub> =2.5 $\Omega$ ,                |     | 22    |      |       |  |
| Turn-off fall time(note3)               | tf               |  |     | 35    |      |       |  |
| Drain-source body diode characteristics |                  |  |     |       |      |       |  |
| Continuous source-drain diode current   | Is               | T <sub>C</sub> =25℃  |     |       | -2.0 | Α     |  |
| Body diode voltage (note 2)             | V <sub>SD</sub>  | I <sub>S</sub> =-2A,VGS =0V                                      |     | -0.83 | -1.2 | V     |  |

### Notes:

- <sup>1)</sup> PRepetitive rating, pulse width limited by junction temperature.
- <sup>2)</sup> Pulse test: pulse width ≤ 300us, duty cycle≤ 2%.
- <sup>3)</sup> These parameters have no way to verify.



# **Typical Characteristics**

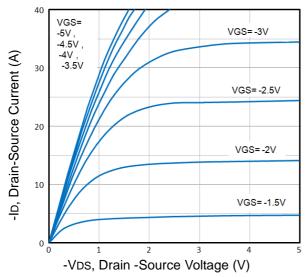


Fig1. Typical Output Characteristics

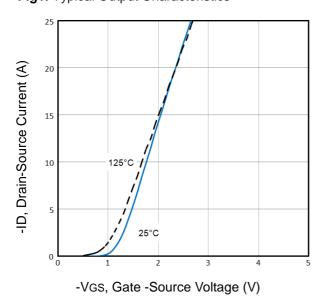


Fig3. Typical Transfer Characteristics

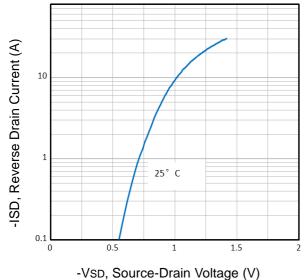


Fig5. Typical Source-Drain Diode Forward Voltage

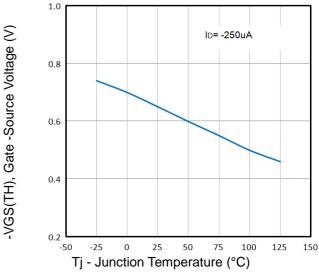


Fig2. Normalized Threshold Voltage Vs. Temperature

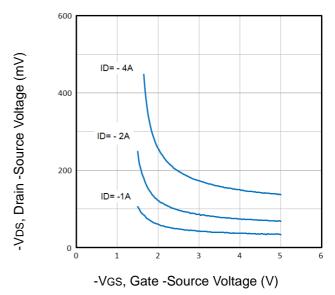
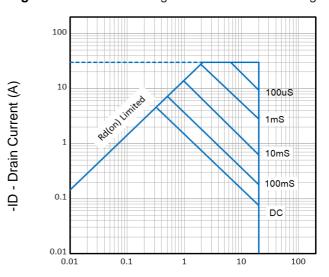


Fig4. Drain -Source Voltage vs Gate -Source Voltage



-VDS, Drain -Source Voltage (V)

Fig6. Maximum Safe Operating Area

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## **Typical Characteristics**

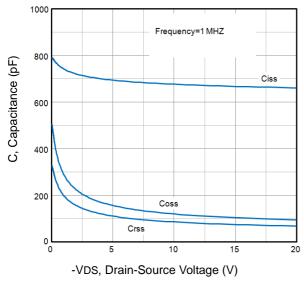


Fig7. Typical Capacitance Vs. Drain-Source Voltage

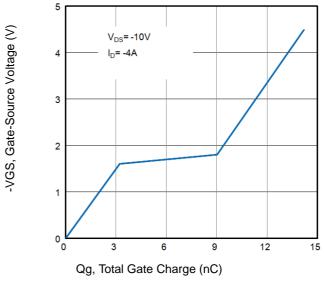


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

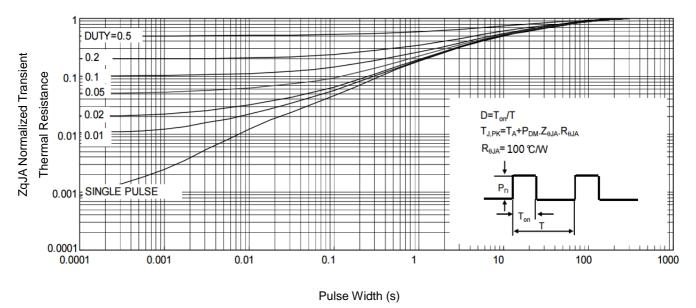


Fig9. Normalized Maximum Transient Thermal Impedance

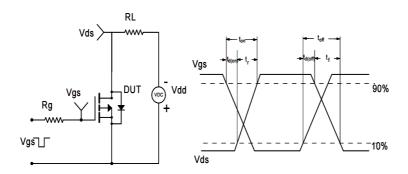


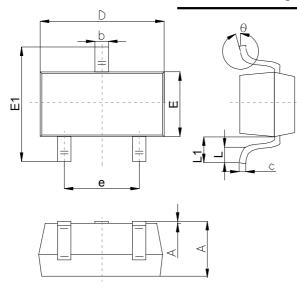
Fig10. Switching Time Test Circuit and waveforms

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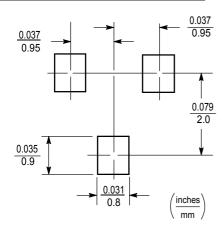
# **Outlitne Drawing**

# SOT-23 Package Outline Dimensions



| Symbol | Dimensions In Millimeters |      |      |  |  |
|--------|---------------------------|------|------|--|--|
|        | Min                       | Тур  | Max  |  |  |
| Α      | 0.90                      |      | 1.40 |  |  |
| A1     | 0.00                      |      | 0.10 |  |  |
| b      | 0.30                      |      | 0.50 |  |  |
| С      | 0.08                      |      | 0.20 |  |  |
| D      | 2.80                      | 2.90 | 3.10 |  |  |
| Е      | 1.20                      |      | 1.60 |  |  |
| E1     | 2.25                      |      | 2.80 |  |  |
| е      | 1.80                      | 1.90 | 2.00 |  |  |
| L      | 0.10                      |      | 0.50 |  |  |
| L1     | 0.4                       |      | 0.55 |  |  |
| θ      | 0°                        |      | 10°  |  |  |

# **Suggested Pad Layout**



Note:

Controlling

dimension:in/millimeters. 2.General

tolerance: ±0.05mm.

3. The pad layout is for reference purposes only.

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